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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Team Nexperia

# PEMD14; PUMD14

## NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = open

Rev. 02 — 2 September 2009

**Product data sheet** 

## 1. Product profile

### 1.1 General description

NPN/PNP resistor-equipped transistors

Table 1. Product overview

Type number			Package		PNP/PNP complement	NPN/NPN complement	
	NXP	JEITA					
PEMD14	SOT666	-	PEMB14	PEMH14			
PUMD14	SOT363	SC-88	PUMB14	PUMH14			

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ



## 2. Pinning information

Table 3. Pinning

Table 0.	19		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R1
			1 2 3 006aaa269

## 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMD14	-	plastic surface mounted package; 6 leads	SOT666
PUMD14	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD14	5B
PUMD14	T2*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	vith negative polar	ity		
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		[1] [2] _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		[1] [2] _	300	mW

<sup>[1]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25  ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1] [2]	-	625	K/W
Per device						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2] -	-	416	K/W

<sup>[1]</sup> Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

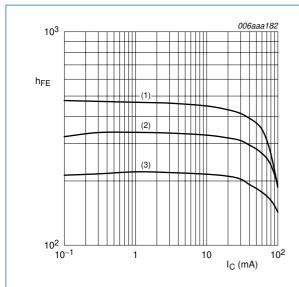
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

## 7. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified

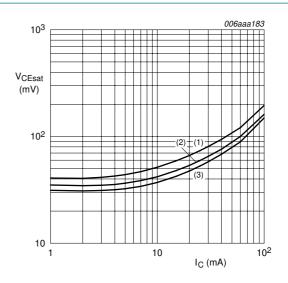
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor; for the PNP transis	tor with negative polarity				
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	the PNP transistor with negative polarity stor-base cut-off $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$ 100 stor-emitter $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$ 1 1 $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ 50 $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ 100 stor-base cut-off $V_{CE} = 30 \text{ V}; I_C = 0 \text{ A}$ 100 stor-enitter $V_{CE} = 5 \text{ V}; I_C = 0 \text{ A}$ 100 stor-emitter $V_{CE} = 5 \text{ V}; I_C = 1 \text{ mA}$ 100 150 stor-emitter $V_{CE} = 5 \text{ V}; I_C = 1 \text{ mA}$ 100 150 stor-enitter $V_{CE} = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ - 150 stor capacitance $V_{CB} = -10 \text{ V}; I_C = 10 \text{ A};$ $V_{CE} = 10 \text{ M};$	μΑ			
	cut-off current	02 , 5 ,	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		33	47	61	kΩ
C <sub>c</sub>	collector capacitance	02 12 0				
	TR1 (NPN)		-	-	2.5	рF
	TR2 (PNP)		-	-	3	pF



$$V_{CE} = 5 V$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \,^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

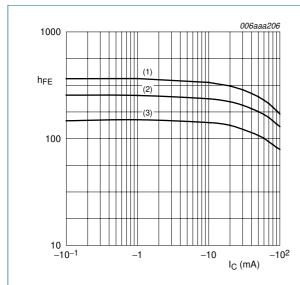
Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \,^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

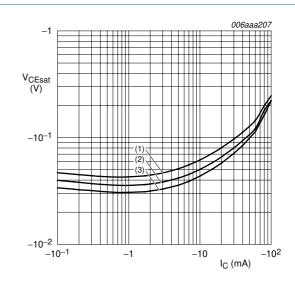
Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values





- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \,^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 3. TR2 (PNP): DC current gain as a function of collector current; typical values



$$I_C/I_B = 20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \,^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 4. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

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## 8. Package outline

#### Plastic surface-mounted package; 6 leads

**SOT363** 

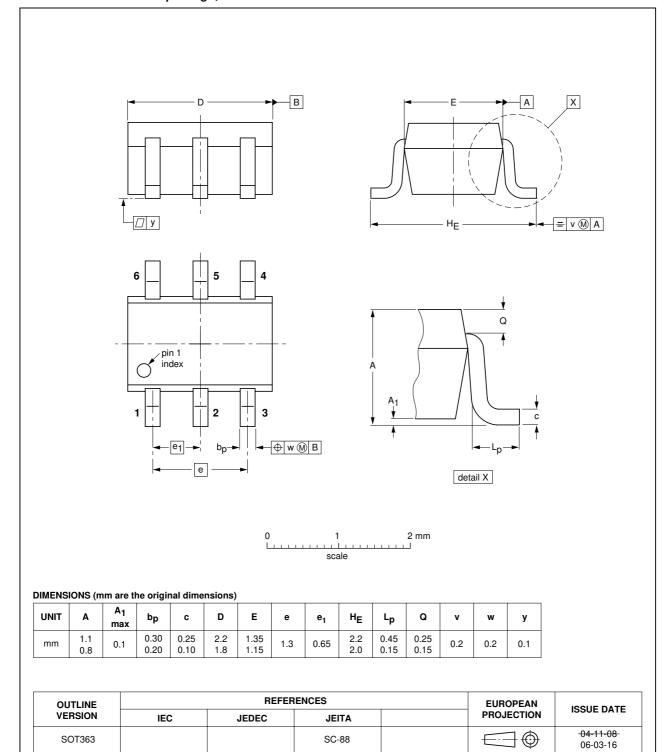


Fig 5. Package outline SOT363 (SC-88)

### Plastic surface-mounted package; 6 leads

**SOT666** 

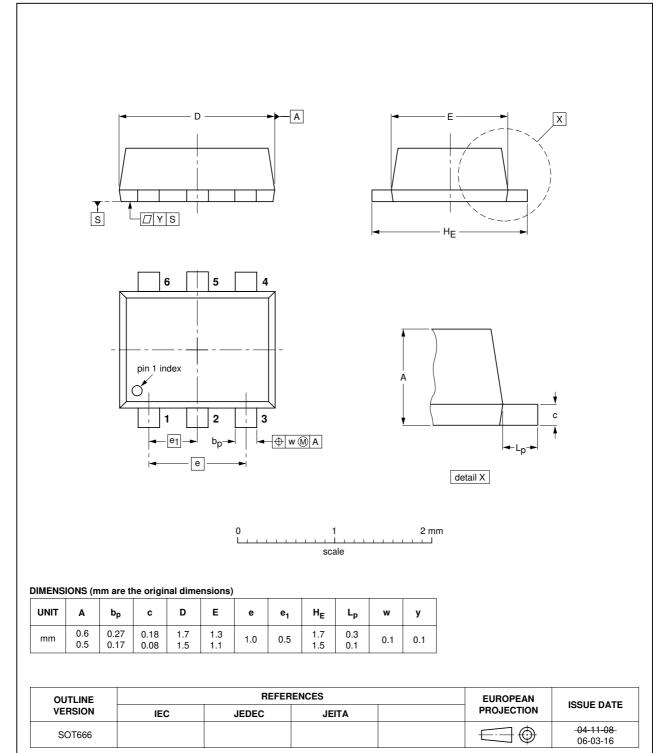


Fig 6. Package outline SOT666

## 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing qua	ntity	
			3000	4000	10000
PEMD14	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T1 [2]	-115	-	-135
PUMD14	SOT363	4 mm pitch, 8 mm tape and reel; T2 [3]	-125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

## 10. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD14_PUMD14_2	20090902	Product data sheet	-	PEMD14_PUMD14_1
Modifications:	<ul> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> </ul>			
	<ul> <li>Figure 5 "Pad</li> </ul>	ckage outline SOT363 (SC	<u>-88)"</u> : updated	
	<ul> <li>Figure 6 "Pad</li> </ul>	ckage outline SOT666": up	dated	
PEMD14_PUMD14_1	20050114	Product data sheet	-	-

### 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PEMD14; PUMD14

## NPN/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

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